

N-Channel MOSFET

General Description

The WSD3072DN33 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

The WSD3072DN33 meet the RoHS and Green Product requirement, 100% E_{AS} guaranteed with full function reliability approved.

Product Summery

BV _{DSS}	R _{DS(ON)}	I _D
30V	3.5mΩ	72A

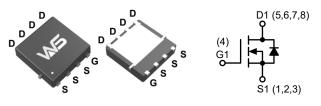
Applications

- Battery protection
- Load switch
- Uninterruptible power supply

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% E_{AS} Guaranteed
- Green Device Available

DFN3X3-8L Pin Configuration



Absolute Maximum Ratings (T_C=25°C, Unless Otherwise Noted)

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	30	V	
V _{GS}	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	72		
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	48	А	
I _{DM}	Pulsed Drain Current ²	160		
E _{AS}	Single Pulse Avalanche Energy ³	315	mJ	
I _{AS}	Avalanche Current	38	А	
P _D @T _C =25°C	Total Power Dissipation ⁴	59	W	
T _{STG}	Storage Temperature Range -55 to 150		°C	
TJ	Operating Junction Temperature Range	-55 to 150	U U	

Thermal Data

Symbol	Parameter	Тур.	Max.	Units	
R _{θJA}	Thermal Resistance, Junction-to-Ambient ¹		62	°C/W	
R _{θJC}	Thermal Resistance, Junction-to-Case ¹	sistance, Junction-to-Case ¹			



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Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250µA	30			V	
D	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =30A		3.5	4.5	- mΩ	
R _{DS(ON)}		V _{GS} =4.5V , I _D =15A		6.5	8.5		
V _{GS(th)}	Gate Threshold Voltage		1.0	1.6	2.5	V	
$\Delta V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	- V _{GS} =V _{DS} , Ι _D =250μΑ		-6.16		mV/°C	
	Drain-Source Leakage Current	V_{DS} =24V , V_{GS} =0V , T_{J} =25°C			1.0	μA	
I _{DSS}	Drain-Source Leakage Current	V_{DS} =24V , V_{GS} =0V , T_{J} =55°C			5.0		
I _{GSS}	Gate-Source Leakage Current	V_{GS} =±20V, V_{DS} =0V			±100	nA	
9 _{fs}	Forward Transconductance	V _{DS} =5V , I _D =30A		22		S	
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f = 1.0MHz		1.7	3.4	Ω	
Qg	Total Gate Charge (4.5V)			20			
Q _{gs}	Gate-Source Charge	V _{DS} =15V,V _{GS} =4.5V,I _D =15A		7.6		nC	
Q _{gd}	Gate-Drain Charge			7.2			
T _{d(on)}	Turn-On Delay Time			7.8			
Tr	Rise Time			15			
T _{d(off)}	Turn-Off Delay Time	R _G =3.3Ω , I _D =15A		37.3		ns	
T _f	Fall Time			10.5			
C _{iss}	Input Capacitance			2295			
C _{oss}	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f = 1.0MHz		267		pF	
C _{rss}	Reverse Transfer Capacitance			210			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
ا _S	Continuous Source Current ^{1,6}	· V _G =V _D =0V,Force Current			80	А
I _{SM}	Pulsed Source Curren ^{2,6}				160	А
V _{SD}	Diode Forward Voltage ²	V_{GS} =0V , I_{S} =1A , T_{J} =25°C			1.0	V
t _{rr}	Reverse Recovery Time	l _F =30A, dl/dt=100A/µs , T _J =25°C		14		ns
Q _{rr}	Reverse Recovery Charge	$T_{\rm F}$ = 30A, u/dl = 100A/µs , $T_{\rm J}$ = 25 C		5		nC

Note:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2. The data tested by pulsed , pulse width \leq 300µs , duty cycle \leq 2%

3. The $\,E_{AS}\,$ data shows Max. rating . The test condition is $\,V_{DD}$ =24V, V_{GS} =10V, L=0.5mH, I_{AS} =38A

4. The power dissipation is limited by 150°C junction temperature.

5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



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Typical Characteristics

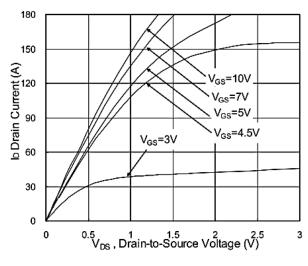


Fig.1 Typical Output Characteristics

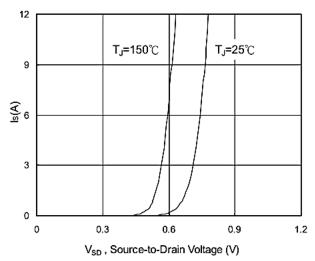
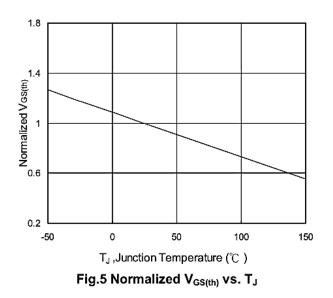
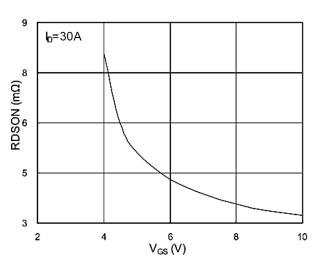
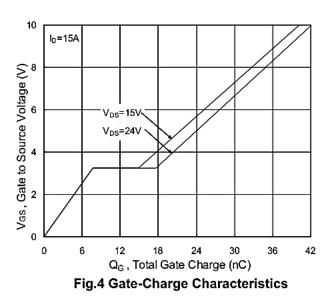


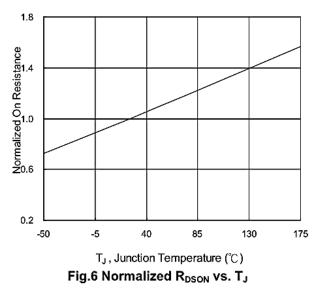
Fig.3 Forward Characteristics of Reverse













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Typical Characteristics (Cont.)

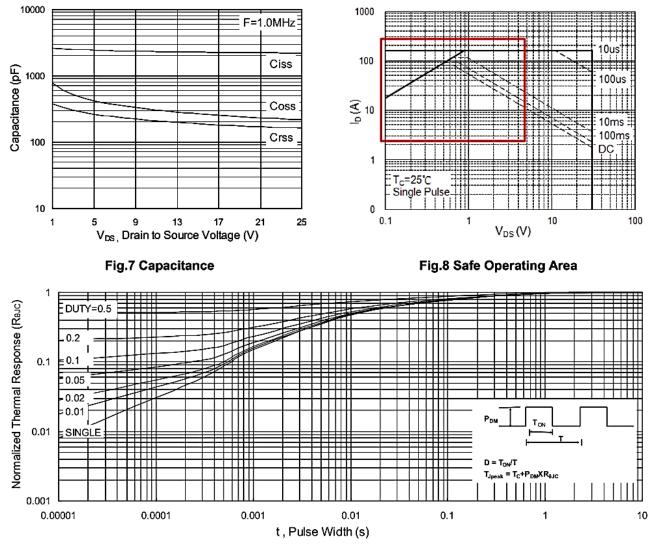


Fig.9 Normalized Maximum Transient Thermal Impedance

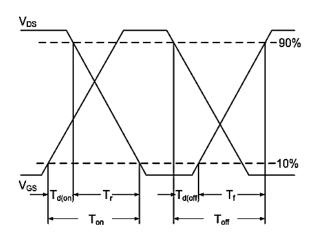


Fig.10 Switching Time Waveform

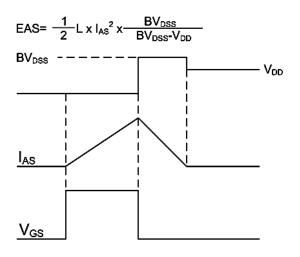
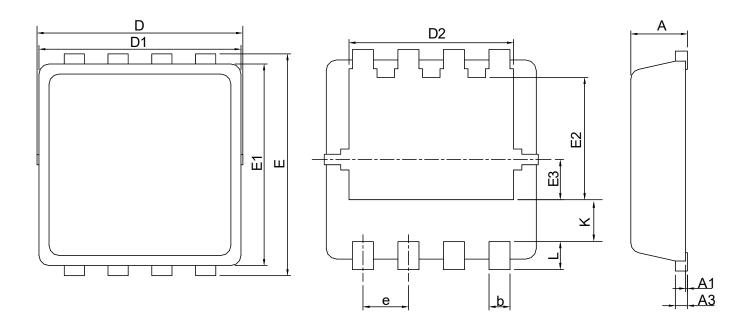


Fig.11 Unclamped Inductive Switching Waveform



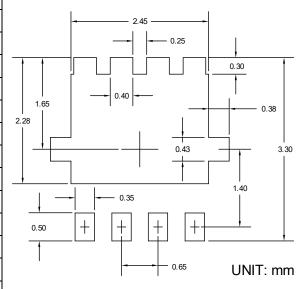
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Packaging information



	DFN3X3-8L				
SYMBOL	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
А	0.80	1.00	0.031	0.039	
A1	0.00	0.05	0.000	0.002	
A3	0.10	0.25	0.004	0.010	
b	0.24	0.35	0.009	0.014	
D	2.90	3.30	0.114	0.130	
D1	2.90	3.10	0.114	0.122	
D2	2.25	2.45	0.089	0.096	
E	3.10	3.30	0.122	0.130	
E1	2.90	3.10	0.114	0.122	
E2	1.65	1.85	0.065	0.073	
E3	0.56	0.58	0.022	0.023	
е	0.65	BSC	0.026	BSC	
K	0.475	0.775	0.019	0.031	
L	0.30	0.50	0.012	0.020	

RECOMMENDED LAND PATTERN





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